

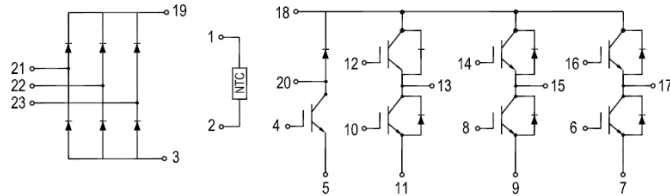


GT10PI120B2FH

IGBT Module

Features:

- Field Stop Trench Gate IGBT
- Short Circuit Rated > 10 μ s
- Low Saturation Voltage
- Low Switching Loss
- 100% RBSOA Tested (2 \times I_c)
- Low Stray Inductance
- Lead Free, Compliant with RoHS Requirement



Applications:

- Industrial Inverters
- Servo Applications

IGBT, Inverter

Maximum Rated Values (T_C=25°C unless otherwise specified)

V _{CES}	Collector-Emitter Blocking Voltage		1200	V
V _{GES}	Gate-Emitter Voltage		±20	V
I _C	Continuous Collector Current	T _C =100°C	10	A
		T _C = 25°C	20	A
I _{CM}	Repetitive Peak Collector Current	T _J =175°C	20	A
t _{SC}	Short Circuit Withstand Time		>10	μs
P _D	Maximum Power Dissipation per IGBT	T _C =25°C T _{Jmax} =175°C	165	W



Electrical Characteristics of IGBT ($T_C=25^\circ\text{C}$ unless otherwise specified)

Static Characteristics

Symbol	Description	Conditions	Min	Typ	Max	Unit
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C=1\text{ mA}, V_{CE}=V_{GE}$	4.5	5.5	6.0	V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=10\text{ A}, V_{GE}=15\text{V}$	$T_J=25^\circ\text{C}$	1.90	2.10	V
			$T_J=125^\circ\text{C}$	2.20		V
I_{CES}	Collector-Emitter Leakage Current	$V_{GE}=0\text{V}, V_{CE}=V_{CES}, T_J=25^\circ\text{C}$			1	mA
I_{GES}	Gate-Emitter Leakage Current	$V_{GE}=\pm 20\text{V}, V_{CE}=0\text{V}, T_J=25^\circ\text{C}$			200	nA
C_{ies}	Input Capacitance	$V_{CE}=25\text{V}, V_{GE}=0\text{V}, f=1\text{MHz}$		1.5		nF
C_{oes}	Output Capacitance			0.1		nF

Switching Characteristics

$t_{d(on)}$	Turn-on Delay Time	$V_{CC}=600\text{V}, I_C=10\text{A}, R_{Gon}=40\ \Omega, V_{GE}=\pm 15\text{V},$ Inductive Load	$T_J=25^\circ\text{C}$	110		ns
			$T_J=125^\circ\text{C}$	105		
t_r	Rise Time		$T_J=25^\circ\text{C}$	35		ns
			$T_J=125^\circ\text{C}$	30		
$t_{d(off)}$	Turn-off Delay Time	$V_{CC}=600\text{V}, I_C=10\text{A}, R_{Goff}=40\ \Omega, V_{GE}=\pm 15\text{V},$ Inductive Load	$T_J=25^\circ\text{C}$	90		ns
			$T_J=125^\circ\text{C}$	105		
t_f	Fall Time		$T_J=25^\circ\text{C}$	350		ns
			$T_J=125^\circ\text{C}$	440		
E_{on}	Turn-on Switching Loss	$V_{CC}=600\text{V}, I_C=10\text{A}, R_{Gon}=40\ \Omega, V_{GE}=\pm 15\text{V},$ $di/dt=220\text{A}/\mu\text{s} (T_J=125^\circ\text{C})$ Inductive Load	$T_J=25^\circ\text{C}$	1.27		mJ
			$T_J=125^\circ\text{C}$	1.48		
E_{off}	Turn-off Switching Loss		$T_J=25^\circ\text{C}$	0.59		mJ
			$T_J=125^\circ\text{C}$	0.70		
Q_g	Total Gate Charge	$V_{GE}=+15\text{V} \dots -15\text{V}$	$T_J=25^\circ\text{C}$	80		nC
RBSOA	$I_C=20\text{A}, V_{CC}=1050\text{V}, V_p=1200\text{V}, R_G=40\ \Omega, V_{GE}=+15\text{V to } 0\text{V}, T_J=150^\circ\text{C}$			Trapezoid		
SCSOA	$V_{CC}=600\text{V}, V_{GE}=15\text{V}, T_J=150^\circ\text{C}$			10		μs
$R_{\theta JC}$	IGBT Thermal Resistance: Junction-To-Case				0.894	$^\circ\text{C}/\text{W}$



Diode, Inverter

Maximum Rated Values ($T_C=25^\circ\text{C}$ unless otherwise specified)

V_{RRM}	Repetitive Peak Reverse Voltage	1200	V
I_F	Diode Continuous Forward Current	10	A
I_{FM}	Diode Maximum Forward Current	20	A

Electrical Characteristics of FWD ($T_C=25^\circ\text{C}$ unless otherwise specified)

Symbol	Description	Conditions	Min	Typ	Max	Unit
V_{FM}	Forward Voltage	$I_F=10\text{ A}$	$T_J=25^\circ\text{C}$	1.70		V
			$T_J=125^\circ\text{C}$	1.80		
I_{rr}	Peak Reverse Recovery Current		$T_J=25^\circ\text{C}$	10		A
			$T_J=125^\circ\text{C}$	12		
Q_{rr}	Reverse Recovery Charge	$I_F=10\text{A}$, $di/dt = 300\text{A}/\mu\text{s}(T_J=125^\circ\text{C})$, $V_{rr}=600\text{V}$, $V_{GE} = -15\text{V}$	$T_J=25^\circ\text{C}$	1.00		μC
			$T_J=125^\circ\text{C}$	1.49		
E_{rec}	Reverse Recovery Energy		$T_J=25^\circ\text{C}$	0.32		mJ
			$T_J=125^\circ\text{C}$	0.56		
$R_{\theta JC}$	Diode Thermal Resistance: Junction-To-Case				1.365	$^\circ\text{C}/\text{W}$

IGBT, Brake-Chopper

Maximum Rated Values ($T_C=25^\circ\text{C}$ unless otherwise specified)

V_{CES}	Collector-Emitter Blocking Voltage		1200	V
V_{GES}	Gate-Emitter Voltage		± 20	V
I_C	Continuous Collector Current	$T_C=100^\circ\text{C}$	10	A
		$T_C=25^\circ\text{C}$	20	A
I_{CM}	Repetitive Peak Collector Current	$T_J = 175^\circ\text{C}$	20	A
t_{sc}	Short Circuit Withstand Time		>10	μs
P_D	Maximum Power Dissipation per IGBT	$T_C = 25^\circ\text{C}$ $T_{Jmax}=175^\circ\text{C}$	165	W



Electrical Characteristics of IGBT ($T_C=25^\circ\text{C}$ unless otherwise specified)

Static Characteristics

Symbol	Description	Conditions	Min	Typ	Max	Unit
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C = 1 \text{ mA}, V_{CE} = V_{GE}$	4.5	5.5	6.0	V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 10 \text{ A}, V_{GE} = 15 \text{ V}$	$T_J = 25^\circ\text{C}$	1.90	2.10	V
			$T_J = 125^\circ\text{C}$	2.20		V
I_{CES}	Collector-Emitter Leakage Current	$V_{GE} = 0 \text{ V}, V_{CE} = V_{CES}, T_J = 25^\circ\text{C}$			1	mA
I_{GES}	Gate-Emitter Leakage Current	$V_{GE} = \pm 20 \text{ V}, V_{CE} = 0 \text{ V}, T_J = 25^\circ\text{C}$			200	nA
C_{ies}	Input Capacitance	$V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}, f = 1 \text{ MHz}$		1.5		nF
C_{oes}	Output Capacitance			0.1		nF

Switching Characteristics

$t_{d(on)}$	Turn-on Delay Time	$V_{CC} = 600 \text{ V}, I_C = 10 \text{ A}, R_{Gon} = 40 \Omega, V_{GE} = \pm 15 \text{ V},$ Inductive Load	$T_J = 25^\circ\text{C}$	110		ns
			$T_J = 125^\circ\text{C}$	105		
t_r	Rise Time		$T_J = 25^\circ\text{C}$	35		ns
			$T_J = 125^\circ\text{C}$	30		
$t_{d(off)}$	Turn-off Delay Time	$V_{CC} = 600 \text{ V}, I_C = 10 \text{ A}, R_{Goff} = 40 \Omega, V_{GE} = \pm 15 \text{ V},$ Inductive Load	$T_J = 25^\circ\text{C}$	90		ns
			$T_J = 125^\circ\text{C}$	105		
t_f	Fall Time		$T_J = 25^\circ\text{C}$	350		ns
			$T_J = 125^\circ\text{C}$	440		
E_{on}	Turn-on Switching Loss	$V_{CC} = 600 \text{ V}, I_C = 10 \text{ A}, R_{Gon} = 40 \Omega, V_{GE} = \pm 15 \text{ V},$ $di/dt = 220 \text{ A}/\mu\text{s} (T_J = 125^\circ\text{C})$ Inductive Load	$T_J = 25^\circ\text{C}$	1.27		mJ
			$T_J = 125^\circ\text{C}$	1.48		
E_{off}	Turn-off Switching Loss		$T_J = 25^\circ\text{C}$	0.59		mJ
			$T_J = 125^\circ\text{C}$	0.70		
Q_g	Total Gate Charge	$V_{GE} = +15 \text{ V} \dots -15 \text{ V}$	$T_J = 25^\circ\text{C}$	80		nC
RBSOA	$I_C = 20 \text{ A}, V_{CC} = 1050 \text{ V}, V_p = 1200 \text{ V}, R_G = 40 \Omega, V_{GE} = +15 \text{ V to } 0 \text{ V}, T_J = 150^\circ\text{C}$			Trapezoid		
SCSOA	$V_{CC} = 600 \text{ V}, V_{GE} = 15 \text{ V}, T_J = 150^\circ\text{C}$			10		μs
$R_{\theta JC}$	IGBT Thermal Resistance: Junction-To-Case				0.894	$^\circ\text{C}/\text{W}$



Diode, Brake-Chopper Maximum Rated Values ($T_C=25^\circ\text{C}$ unless otherwise specified)

V_{RRM}	Repetitive Peak Reverse Voltage	1200	V
I_F	Diode Continuous Forward Current	10	A
I_{FM}	Diode Maximum Forward Current	20	A

Electrical Characteristics of FWD ($T_C=25^\circ\text{C}$ unless otherwise specified)

Symbol	Description	Conditions		Min	Typ	Max	Unit
V_{FM}	Forward Voltage	$I_F=10\text{A}$	$T_J=25^\circ\text{C}$		1.70		V
			$T_J=125^\circ\text{C}$		1.80		
I_{rr}	Peak Reverse Recovery Current		$T_J=25^\circ\text{C}$		10		A
			$T_J=125^\circ\text{C}$		12		
Q_{rr}	Reverse Recovery Charge	$I_F=10\text{A}$, $di/dt=300\text{A}/\mu\text{s}(T_J=125^\circ\text{C})$, $V_{rr}=600\text{V}$, $V_{GE}=-15\text{V}$	$T_J=25^\circ\text{C}$		1.00		μC
			$T_J=125^\circ\text{C}$		1.49		
E_{rec}	Reverse Recovery Energy		$T_J=25^\circ\text{C}$		0.32		mJ
			$T_J=125^\circ\text{C}$		0.56		
$R_{\theta JC}$	Diode Thermal Resistance: Junction-To-Case					1.365	$^\circ\text{C}/\text{W}$

Diode, Rectifier ($T_C=25^\circ\text{C}$ unless otherwise specified)

V_{RRM}	Repetitive Peak Reverse Voltage	$T_J=25^\circ\text{C}$	1600	V
I_{FRMSM}	Maximum RMS Forward Current per Chip	$T_J=80^\circ\text{C}$	20	A
I_{RMSM}	Maximum RMS Current at Rectifier Output	$T_J=80^\circ\text{C}$	30	A
I_{FSM}	Surge Current @ $t_p=10\text{ms}$	$T_J=25^\circ\text{C}$	300	A
		$T_J=150^\circ\text{C}$	250	
I^2t	I^2t - value	$T_J=25^\circ\text{C}$	450	A^2s
		$T_J=150^\circ\text{C}$	300	



Electrical Characteristics of Diode ($T_C=25^\circ\text{C}$ unless otherwise specified)

V_F	Forward Voltage	$I_F=10\text{ A}$	$T_J=25^\circ\text{C}$		1.10	V	
			$T_J=150^\circ\text{C}$		1.00		
I_R	Reverse Current	$V_R=1600\text{V}$	$T_J=25^\circ\text{C}$			1	mA
$R_{\theta JC}$	Diode Thermal Resistance: Junction-To-Case					1.04	$^\circ\text{C}/\text{W}$

Internal NTC-Thermistor Characteristic

R_{25}	$T_C = 25^\circ\text{C}$	22.7		k Ω
$\Delta R/R$	$T_C = 100^\circ\text{C}$, $R_{100} = 1481\text{ K}\Omega$		± 3	%
P_{25}	$T_C = 25^\circ\text{C}$	5		mW
$B_{25/50}$	$R_2=R_{25} \exp[B_{25/50}(1/T_2-1/(298.15\text{K}))]$	3950		K
$B_{25/80}$	$R_2=R_{25} \exp[B_{25/100}(1/T_2-1/(298.15\text{K}))]$	4000		K

Module

Symbol	Description	Min	Typ	Max	Unit
V_{iso}	Isolation Voltage (All Terminals Shorted)	DC Test Voltage, t=3s	3500		V
Internal Isolation		Al ₂ O ₃			
d_{creep}	Creepage Distance	12.7			mm
d_{clear}	Clearance	12.7			mm
T_J	Maximum Junction Temperature			175	$^\circ\text{C}$
T_{JOP}	Maximum Operating Junction Temperature Range	-40		+150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-40		+125	$^\circ\text{C}$
CTI	Comparative Tracking Index	200			
$R_{\theta CS}$	Case-To-Sink Thermally (Conductive Grease Applied)			0.1	$^\circ\text{C}/\text{W}$
T	Mounting Screw:M4	0.75		1.2	N·m
G	Weight		24		g



Ordering Information Table

Device code	G	T	10	PI	120	B2F	H
	①	②	③	④	⑤	⑥	⑦

- ① - IGBT Module
- ② - Trench & Field Stop IGBT IGBT
- ③ - Rated Current (10=10A)
- ④ - Circuit Configuration (Power Integrated)
- ⑤ - Rated Voltage (120=1200V)
- ⑥ - Package Type
- ⑦ - Test Level (Pass the Important Reliability Test-Industrial Grade)

DATA SHEET

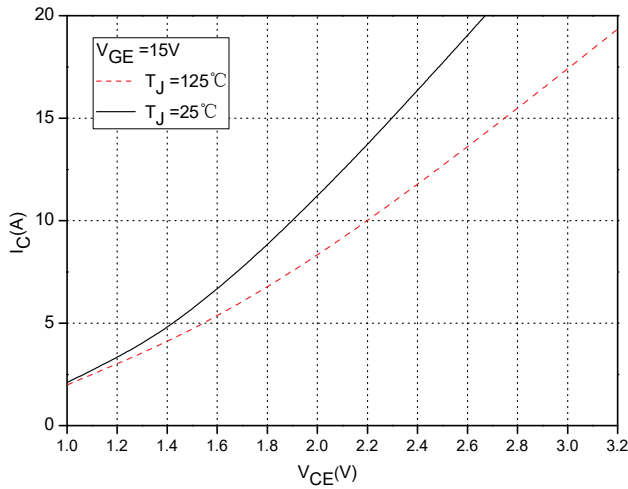


Fig.1 Typical Saturation Voltage Characteristics (Inverter)

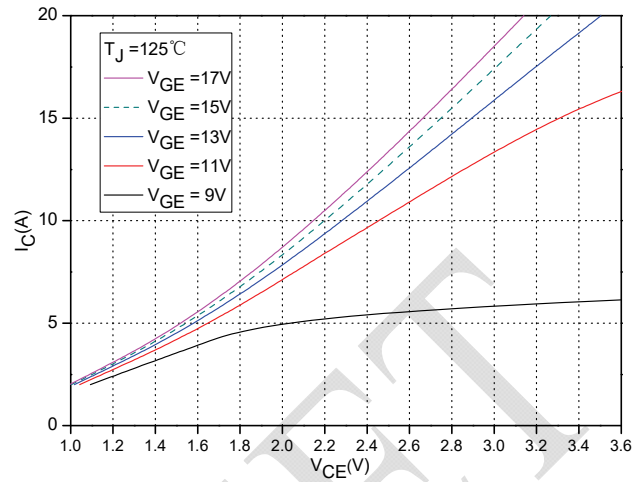


Fig.2 Typical Output Characteristics (Inverter)

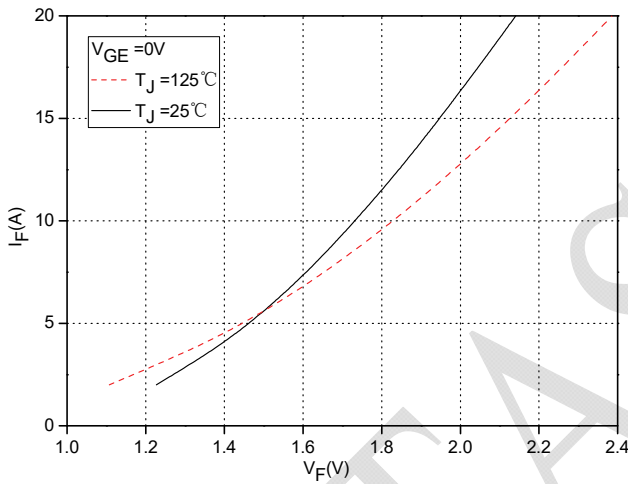


Fig.3 Forward Characteristics of FWD (Inverter)

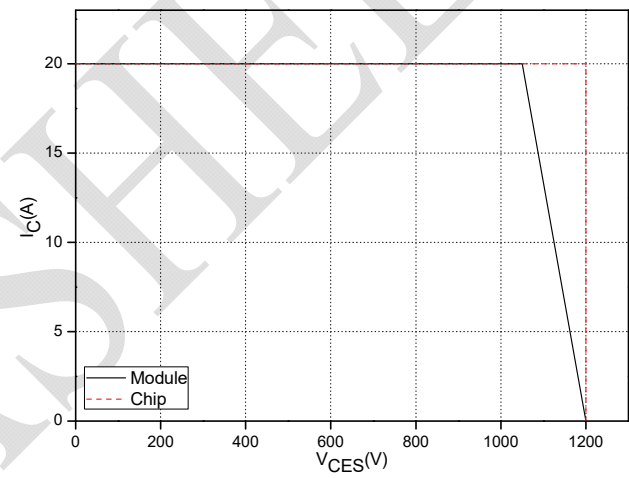


Fig.4 Reverse Bias Safe Operation Area (RBSOA)

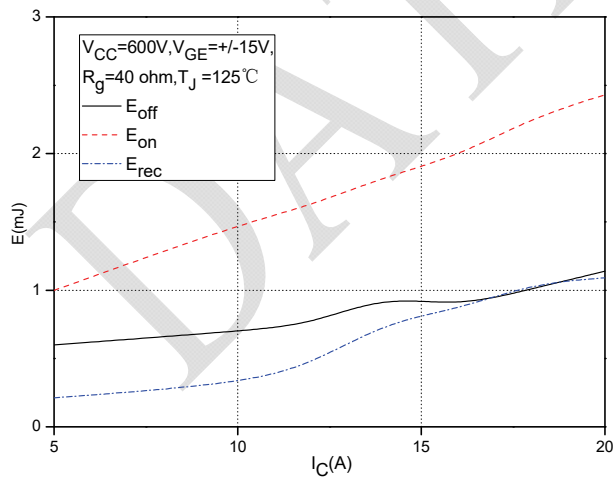


Fig.5 Typical Switching Loss vs. Collector Current (Inverter)

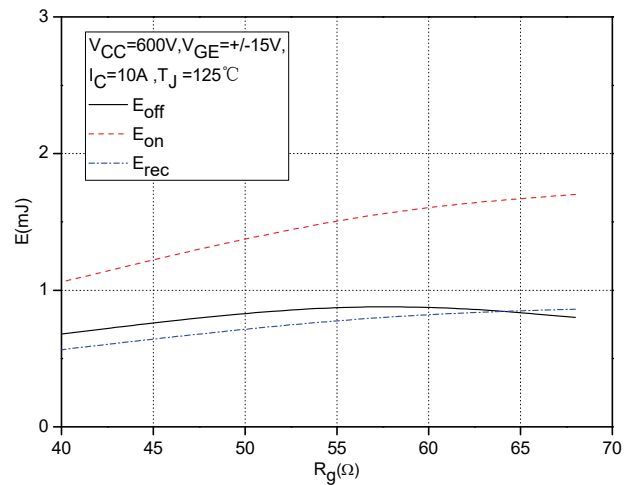


Fig.6 Typical Switching Loss vs. Gate Resistance (Inverter)

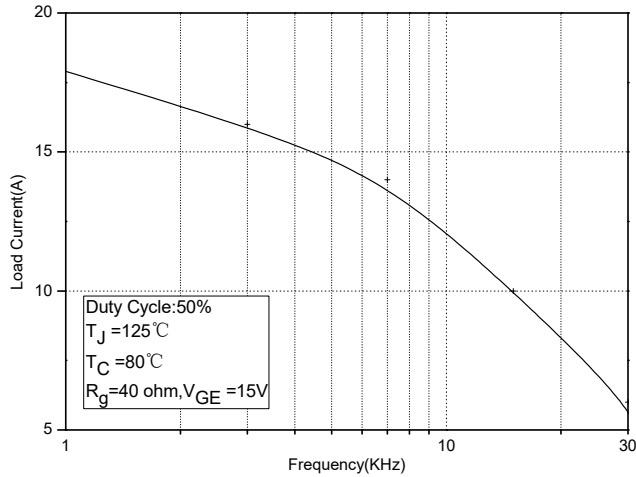


Fig.7 Typical Load Current vs. Frequency (Inverter)

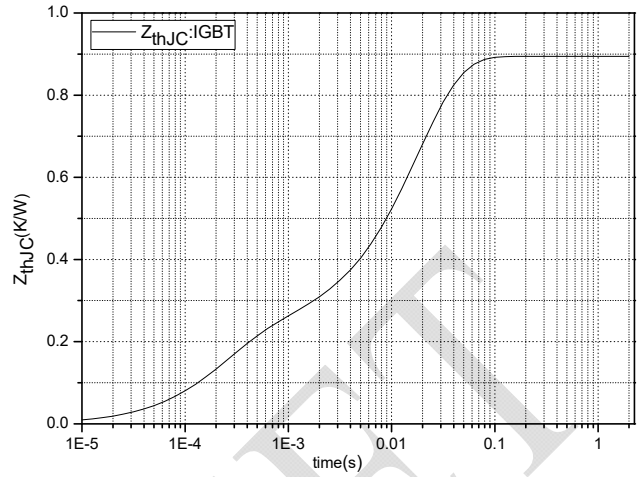


Fig.8 Transient Thermal Impedance (Inverter- IGBT)

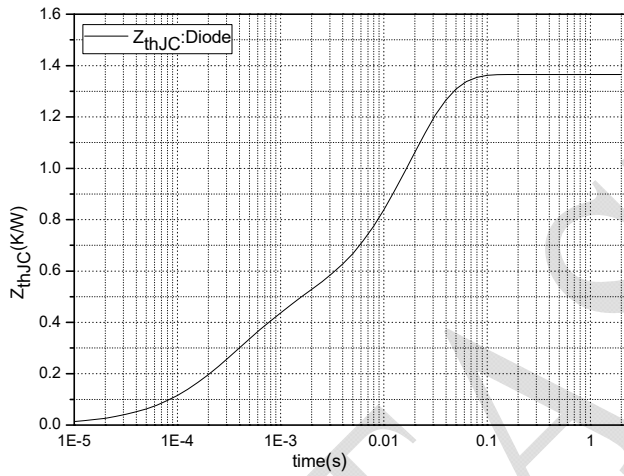


Fig.9 Transient Thermal Impedance (Inverter- Diode)

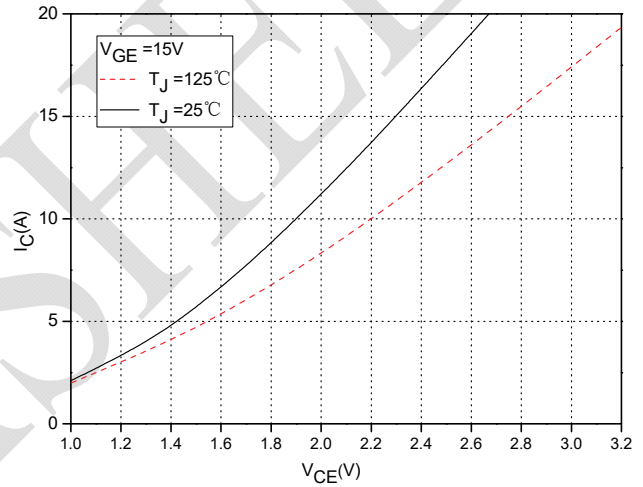


Fig.10 Typical Saturation Voltage Characteristics (Brake-Chopper)

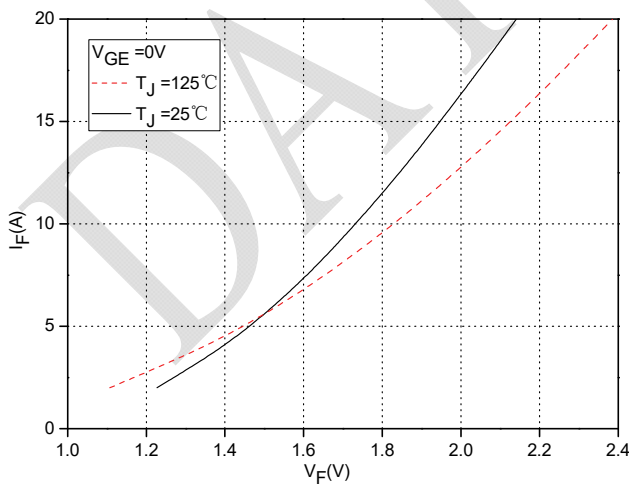


Fig.11 Forward Characteristics of Diode (Brake-Chopper)

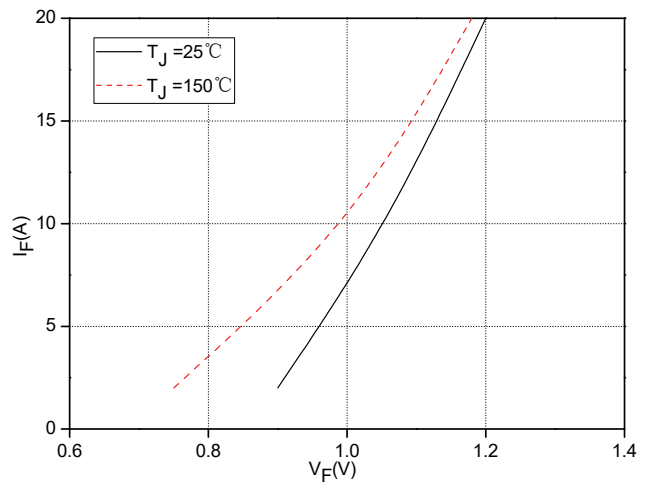


Fig.12 Forward Characteristics of Diode (Rectifier)

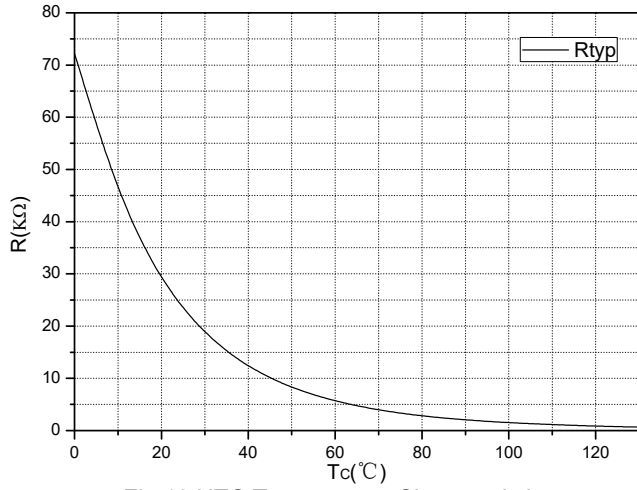
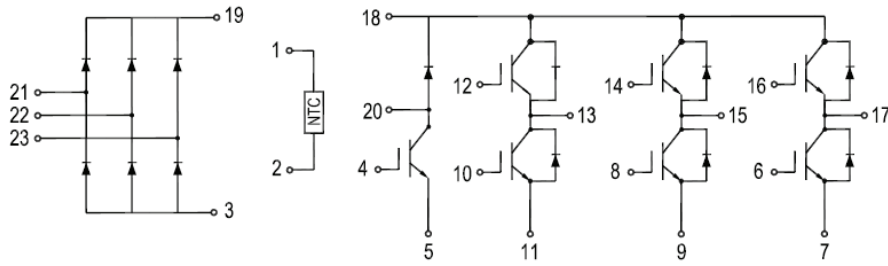


Fig.13 NTC Temperature Characteristics

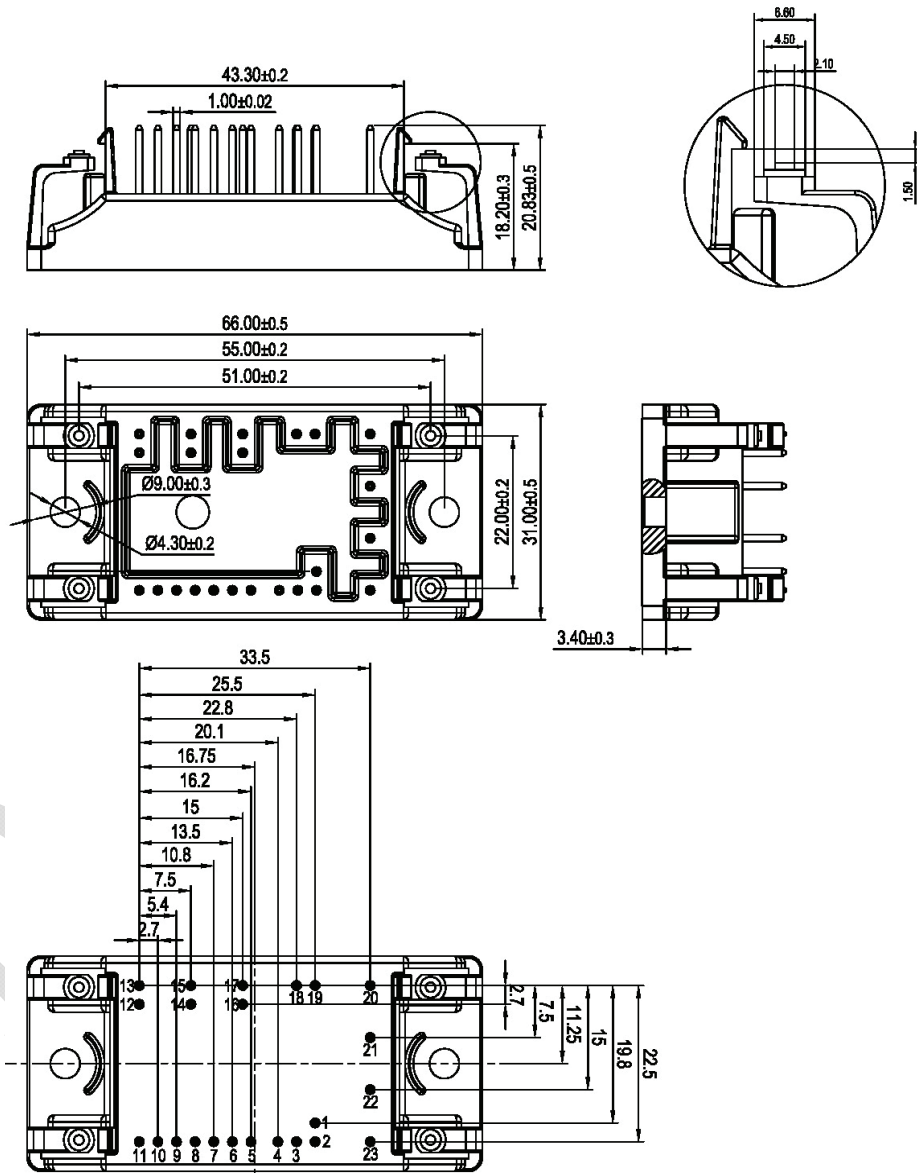
DATA SHEET



Internal Circuit:



Package Outline (Unit: mm):



Unless otherwise specified, dimensions are in millimeters.



Date	Revision	Notes
01/17/2021	A	Final Version

Announcement

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The datasheet with “REV.” + “Arabic numerals” is based on engineering data for initial reference purpose only.

The released datasheet would be issued with “REV.” + “alphabet characters”.

DATA SHEET